



PSMN072-100MSE

N-channel 100 V, 76 mOhm standard level ASFET with enhanced SOA in LPAK33 package. Recommended for fault tolerant applications including high power PoE, inrush management, eFuse and relay replacement

2 October 2023

Objective data sheet

1. General description

New standards and proprietary approaches are enabling Power-over-Ethernet (PoE) systems capable of delivering up to 90 W to each powered device (PD). Such solutions place increased demands on the power sourcing equipment (PSE) in terms of “soft-start”, thermal management and power density requirements. These ASFETs combine enhanced SOA in a compact 3.3 mm x 3.3 mm footprint making them ideally placed for a variety of applications including HP-PoE, eFuse and relay replacement.

2. Features and benefits

- Enhanced safe operating area (SOA) for superior linear mode operation
- Low R_{DSon} for low I^2R losses
- Ultra reliable LPAK33 package for superior thermal and ruggedness performance
- Very low I_{DSS} leakage

3. Applications

- PoE applications
- IEEE802.3at and proprietary PoE solutions
- Fault tolerant load switch - inrush management and eFuse applications
- Battery management applications
- Relay replacement
- WIFI hotspots
- 5G picocells
- CCTV

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	100	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$	-	-	16	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	45	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ °C}$	-	58	76	mΩ
		$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 100\text{ °C}$	-	91	116	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$I_D = 25\text{ A}; V_{DS} = 50\text{ V}; V_{GS} = 10\text{ V}; T_j = 25\text{ °C}$	[tbd]	0.9	[tbd]	nC
$Q_{G(tot)}$	total gate charge		[tbd]	4.9	[tbd]	nC

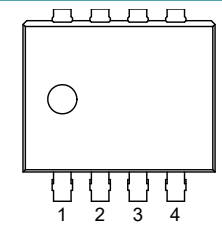
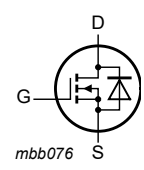
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 9\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; unclamped; $t_p = 13.4\ \mu\text{s}$	[1]	-	-	7.8 mJ
Source-drain diode						
Q_r	recovered charge	$I_S = 25\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 50\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 6	-	21	-	nC

[1] Protected by 100% test

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFPAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN072-100MSE	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN072-100MSE	72ES10

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$; $R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 1	-	45	W
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ }^\circ\text{C}$	-	16	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ }^\circ\text{C}$	-	11	A

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Symbol	Parameter	Conditions	Min	Max	Unit
I_{DM}	peak drain current	pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 2	-	65	A
T_{stg}	storage temperature		-55	175	$^\circ\text{C}$
T_j	junction temperature		-55	175	$^\circ\text{C}$
$T_{sld(M)}$	peak soldering temperature		-	260	$^\circ\text{C}$
Source-drain diode					
I_S	source current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	16	A
I_{SM}	peak source current	pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	65	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 9 \text{ A}$; $V_{sup} \leq 100 \text{ V}$; $R_{GS} = 50 \Omega$; $V_{GS} = 10 \text{ V}$; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; unclamped; $t_p = 13.4 \mu\text{s}$	[1]	-	7.8 mJ
I_{AS}	non-repetitive avalanche current	$V_{sup} = 100 \text{ V}$; $V_{GS} = 10 \text{ V}$; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; $R_{GS} = 50 \Omega$	[1]	-	9 A

[1] Protected by 100% test

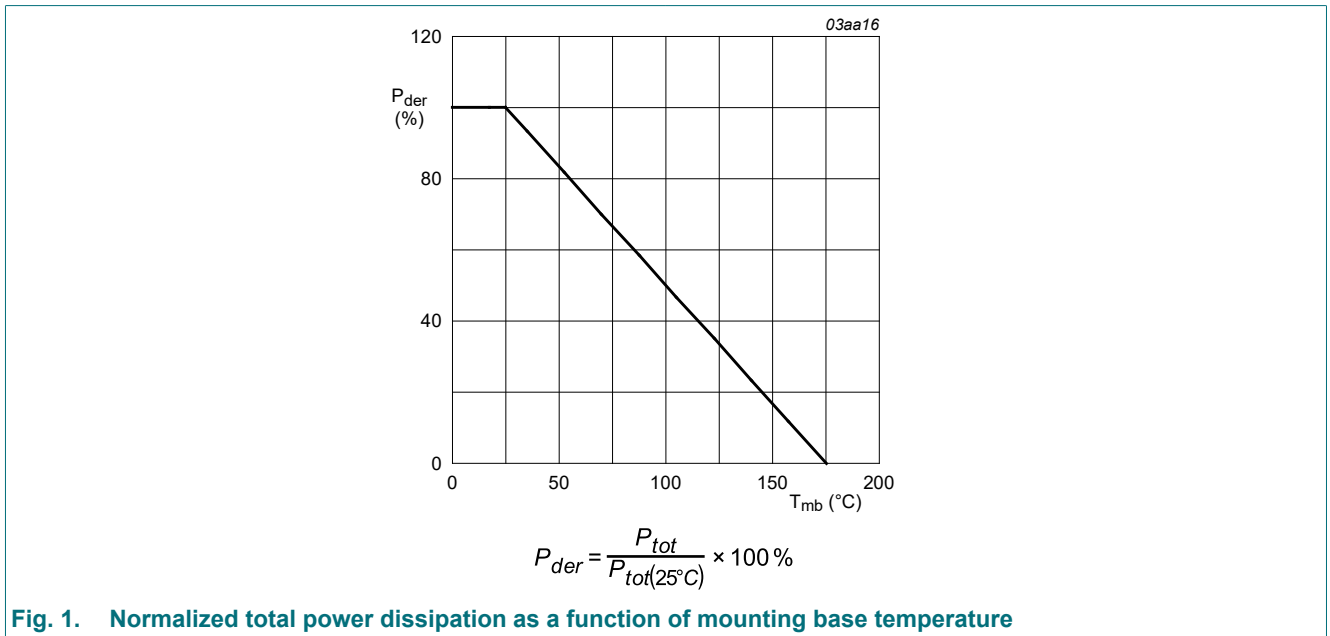
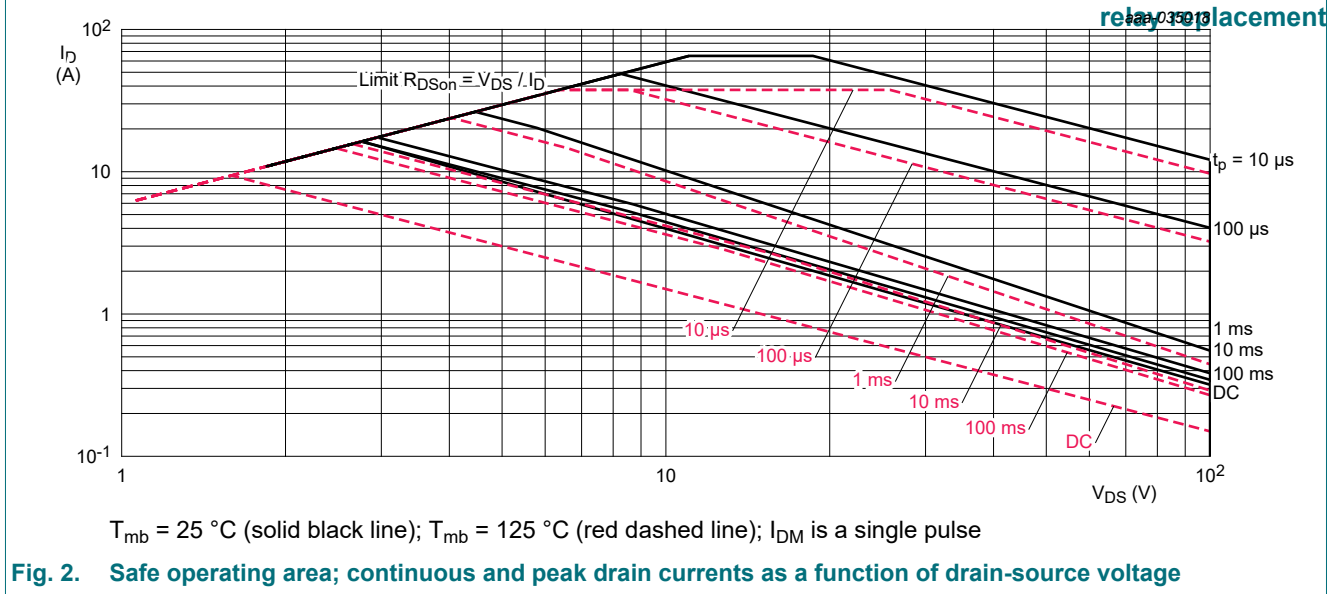


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

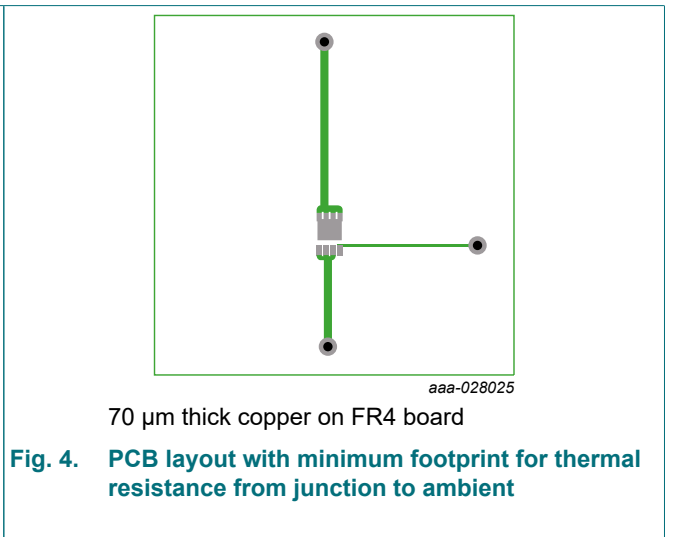
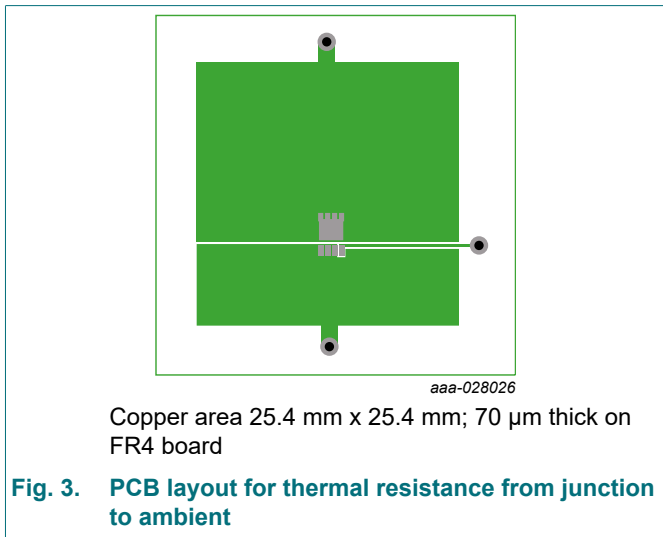
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	[tbd]	3.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 3	-	50	-	K/W
		Fig. 4	-	130	-	K/W



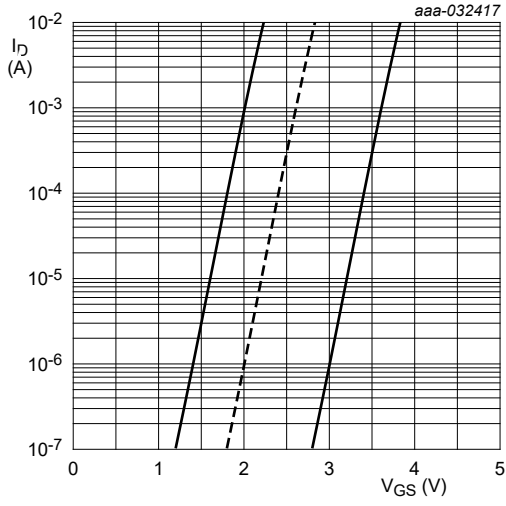
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C; \text{ Fig. 5}$	2	2.6	3.6	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$	-	[tbd]	-	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$	-	[tbd]	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	[tbd]	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	[tbd]	1	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{DS} = 20 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{DS} = -20 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ C$	-	58	76	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ }^\circ C$	-	91	116	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 \text{ }^\circ C$	-	128	172	m Ω
R_G	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	[tbd]	1.2	[tbd]	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C$	[tbd]	4.9	[tbd]	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	2.6	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C$	[tbd]	1.4	[tbd]	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	0.9	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.5	-	nC
Q_{GD}	gate-drain charge		[tbd]	0.9	[tbd]	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; T_j = 25 \text{ }^\circ C$	-	4.5	-	V
C_{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	[tbd]	345	[tbd]	pF
C_{oss}	output capacitance		[tbd]	76	[tbd]	pF
C_{rss}	reverse transfer capacitance		[tbd]	2.4	[tbd]	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \text{ }^\circ \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 5 \text{ }^\circ \Omega; T_j = 25 \text{ }^\circ C$	-	1.2	-	ns
t_r	rise time		-	1	-	ns
$t_{d(off)}$	turn-off delay time		-	3	-	ns
t_f	fall time		-	1.5	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	V
t_{rr}	reverse recovery time	$I_S = 25 \text{ A}; di_S/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; \text{ Fig. 6}$	-	30	-	ns
Q_r	recovered charge	$I_S = 25 \text{ A}; di_S/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; T_j = 25 \text{ }^\circ C; \text{ Fig. 6}$	-	21	-	nC

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$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

Fig. 5. Sub-threshold drain current as a function of gate-source voltage

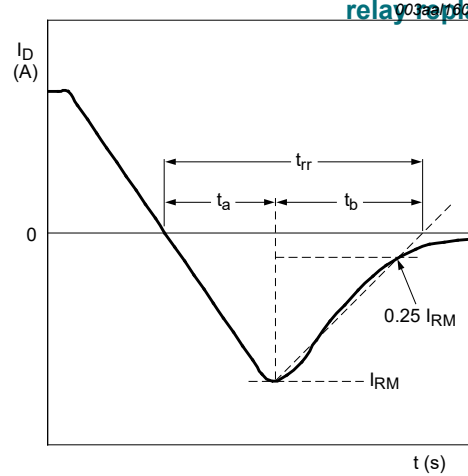


Fig. 6. Reverse recovery timing definition

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11. Package outline

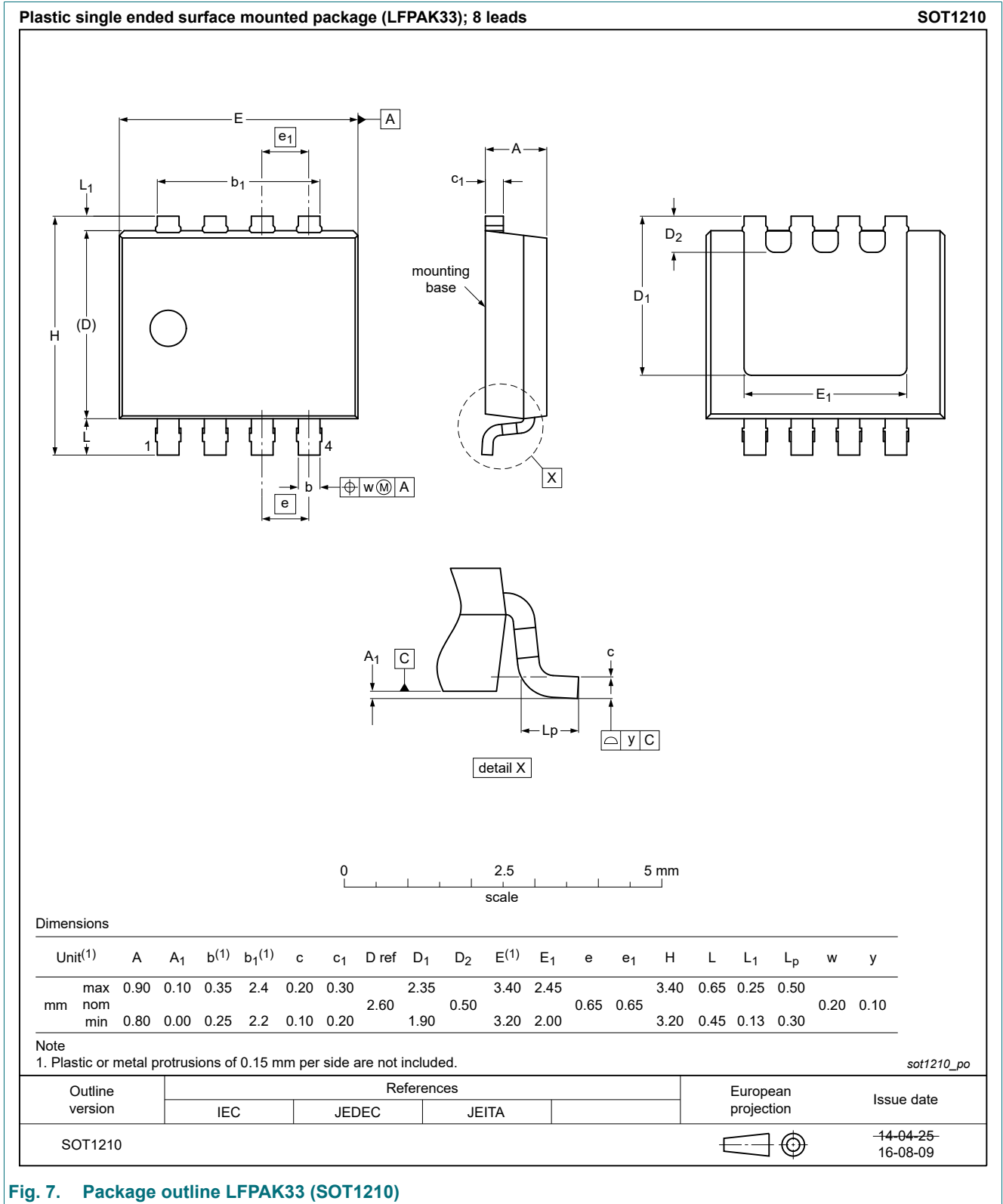


Fig. 7. Package outline LPAK33 (SOT1210)

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12. Soldering

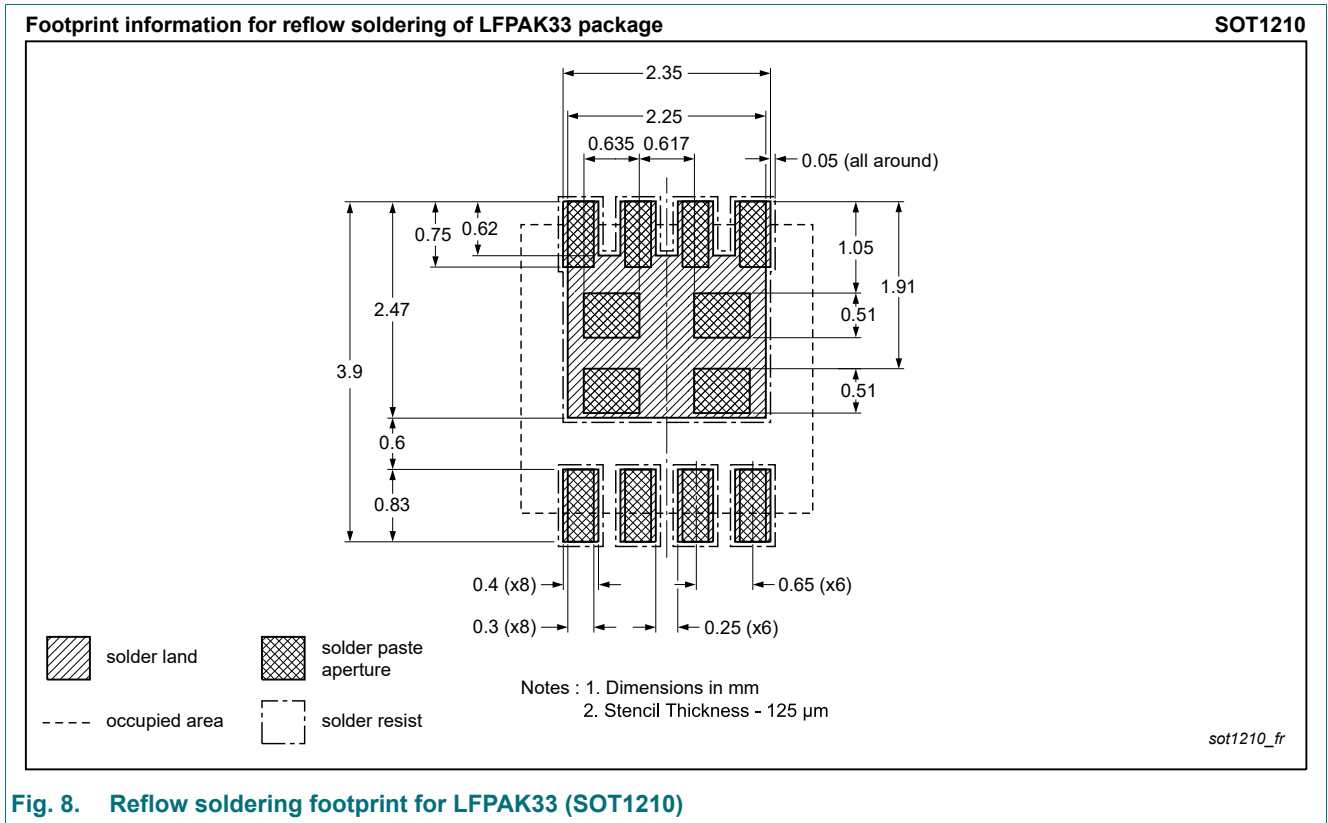


Fig. 8. Reflow soldering footprint for LFPAK33 (SOT1210)

N-channel 100 V, 76 mOhm standard level ASFET with enhanced SOA in LFPK33 package. Recommended for fault tolerant applications including high power PoE, inrush management, eFuse and

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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